Claims

This listing of claims is intended to replace all prior versions, and listings, of claims in this patent application:

- 1. (currently amended) A liquid crystal display device, comprising:
 - at least two storage capacitors disposed between a gate line and a capacitor electrode <u>formed above the gate line</u>, said gate line being connected, via a contact hole passing through said at least two storage capacitors, to the capacitor electrode.
- 2. (previously presented) The liquid crystal display device as claimed in claim 1, wherein the capacitor electrode is made from a transparent conductive material selected from the group consisting of indium-tin-oxide, indium-zinc-oxide and indium-tin-zinc-oxide.
- 3. (currently amended) The liquid crystal display device as claimed in claim 1, further comprising:
 - a gate insulating film provided on a substrate;
 - a storage electrode provided on the gate insulating film to overlap the gate line; and
 - a protective layer provided between the storage electrode and the capacitor electrode.
- 4. (previously presented) The liquid crystal display device as claimed in claim 3, wherein the storage capacitor includes:
 - a first storage capacitor provided between the storage electrode and the gate line with the intervening gate insulating film; and

- a second storage capacitor provided between the storage electrode and the capacitor electrode with the intervening protective layer.
- 5. (previously presented) The liquid crystal display device as claimed in claim 4, wherein the first storage capacitor is connected to the second storage capacitor in parallel.
- 6. (previously presented) The liquid crystal display device as claimed in claim 4, wherein the contact hole is at least two holes spaced to each other at a length larger than the width of the storage electrode.
- 7. (previously presented) The liquid crystal display device as claimed in claim 6, wherein the capacitor electrode has a length larger than the storage electrode.
- 8. (previously presented) The liquid crystal display device as claimed in claim 3, further comprising:
 - a gate electrode connected to the gate line; source and drain electrodes provided on the gate insulating film; and a pixel electrode provided on the protective layer to be electrically connected to the drain electrode.
- 9. (previously presented) The liquid crystal display device as claimed in claim 3, wherein the pixel electrode electrically contacts the storage electrode through said contact hole passing through the protective layer.
- 10. (previously presented) The liquid crystal display device as claimed in claim 8, wherein the gate insulating film has a thickness of about 4000Å.

- 11. (previously presented) The liquid crystal display device as claimed in claim 8, wherein the protective layer has a thickness of about 2000Å.
- 12. (currently amended) A method of fabricating a liquid crystal display device, comprising the steps of:

forming a gate line on a substrate;

forming a gate insulating film on the substrate;

forming a storage electrode on the gate insulating film to overlap the gate line;

forming a protective layer on the gate insulating film;

defining at least two contact holes to expose the gate line; and

forming a capacitor electrode electrically contacting the gate line on the

protective layer.

- 13. (previously presented) The method as claimed in claim 12, wherein the capacitor electrode is made from a transparent conductive material selected from the group consisting of indium-tin-oxide, indium-zinc-oxide and indium-tin-zinc-oxide.
- 14. (previously presented) The method as claimed in claim 12, wherein the said least two contact holes are spaced to each other at a length larger than the width of the storage electrode.
- 15. (previously presented) The method as claimed in claim 14, wherein the capacitor electrode has a length larger than the storage electrode.
- 16. (previously presented) The method as claimed in claim 12, further comprising the steps of:

forming a gate electrode connected to the gate line on the substrate; forming a semiconductor layer on the gate insulating film; forming source and drain electrodes on the semiconductor layer; and forming a pixel electrode on the protective layer.

- 17. (previously presented) The method as claimed in claim 16, wherein the pixel electrode electrically contacts the storage electrode through said contact hole passing through the protective layer.
- 18. (previously presented) The method as claimed in claim 16, wherein the gate insulating film has a thickness of about 4000Å.
- 19. (previously presented) The method as claimed in claim 16, wherein the protective layer has a thickness of about 2000Å.